

214019US-2



#8/Amdt A  
9.16.02  
C. Moore

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :  
EIJI SAKAGAMI :EXAMINER: H. WEISS  
SERIAL NO.: 09/955,076 :  
FILED: SEPTEMBER 19, 2001 :GROUP ART UNIT: 2814  
FOR: NONVOLATILE SEMICONDUCTOR MEMORY  
AND METHOD OF FABRICATING THE SAME

RECEIVED  
SEP 19 2002  
TECHNICAL STAFF 280C

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action dated June 6, 2002, please amend the above-identified patent application as follows:

IN THE TITLE

Please amend the title as follows:

NONVOLATILE SEMICONDUCTOR MEMORY HAVING MONOS  
STRUCTURE AND METHOD OF FABRICATING THE SAME USING  
SHALLOW TRENCH ISOLATION

IN THE CLAIMS

Please amend Claim 1 to read as follows:<sup>1</sup>

1. (Amended) A nonvolatile semiconductor memory comprising:  
a semiconductor substrate;

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<sup>1</sup>The changes to Claim 1 are denoted using underscoring and bracketing in the marked-up copy herewith.